Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	138	etch$5 same high near2 density near2 polyethylene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:37
L2	5	etch$5 same high near2 density near2 polyethylene near16 (boat or cassette)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:39
L3	2	etch$5 same high near2 density near2 polyethylene near15 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:39
L4	2	etch$5 same (high near2 density near2 polyethylene or hdpe) near15 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:40
L5	5	etch$5 same (high near2 density near2 polyethylene or hdpe) same (boat or cassette)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:40
L6	160	(high near2 density near2 polyethylene or hdpe) same (boat or cassette)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:40
L7	0	(high near2 density near2 polyethylene or hdpe) near15 (boat or cassette) near15 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:40
L8	2	(high near2 density near2 polyethylene or hdpe or polyethylene) near15 (boat or cassette) near15 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:43
L9	535	(high near2 density near2 polyethylene or hdpe or polyethylene) near15 (boat or cassette)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:43
L10	12	(high near2 density near2 polyethylene or hdpe or polyethylene) near15 (boat or cassette) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 18:40

L11	53	US-3775202-$.DID. OR US-3969195-$.DID. OR US-3986653-$.DID. OR US-3992454-$.DID. OR US-4023936-$.DID. OR US-4078963-$.DID. OR US-4101386-$.DID. OR US-4139348-$.DID. OR US-4197631-$.DID. OR US-4214952-$.DID. OR US-4232060-$.DID. OR US-4272612-$.DID. OR US-4327134-$.DID. OR US-4447824-$.DID. OR US-4448800-$.DID. OR US-4459155-$.DID. OR US-4519914-$.DID. OR US-4530120-$.DID. OR US-4579569-$.DID. OR US-4638553-$.DID. OR US-4699082-$.DID. OR US-4863561-$.DID. OR US-4957583-$.DID. OR US-4971590-$.DID. OR US-4980017-$.DID. OR US-5104501-$.DID. OR US-5152878-$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 18:40
L12	27	US-3775202-$.DID. OR US-3969195-$.DID. OR US-3986653-$.DID. OR US-3992454-$.DID. OR US-4023936-$.DID. OR US-4078963-$.DID. OR US-4101386-$.DID. OR US-4139348-$.DID. OR US-4197631-$.DID. OR US-4214952-$.DID. OR US-4232060-$.DID. OR US-4272612-$.DID. OR US-4327134-$.DID. OR US-4447824-$.DID. OR US-4448800-$.DID. OR US-4459155-$.DID. OR US-4519914-$.DID. OR US-4530120-$.DID. OR US-4579569-$.DID. OR US-4638553-$.DID. OR US-4699082-$.DID. OR US-4863561-$.DID. OR US-4957583-$.DID. OR US-4971590-$.DID. OR US-4980017-$.DID. OR US-5104501-$.DID. OR US-5152878-$.DID.	US-PGPUB; USPAT	OR	ON	2006/01/20 18:41
L13	20	US-5221421-$.DID. OR US-5516399-$.DID. OR US-5593339-$.DID. OR US-5614027-$.DID. OR US-5665473-$.DID. OR US-5712198-$.DID. OR US-5744214-$.DID. OR US-5766979-$.DID. OR US-5840402-$.DID. OR US-5888308-$.DID. OR US-5908819-$.DID. OR US-5929521-$.DID. OR US-5966593-$.DID. OR US-6012966-$.DID. OR US-6187216-$.DID. OR US-6368410-$.DID. OR US-6506254-$.DID. OR US-6569252-$.DID. OR US-6579153-$.DID. OR US-6767840-$.DID.	US-PGPUB; USPAT	OR	ON	2006/01/20 18:41
S1	16	samantha near2 tan.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:19

S2	9	samantha near2 tan.in. and (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:17
S3	8	samantha near2 tan.in. and ultrasonic$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:31
S4	2	"20030000458".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:21
S5	32	ultrasonic$7 near16 (silicon near2 carbide or sic) same acid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:22
S6	28481	ultrasonic$7 near16 (silicon near2 carbide or sic) same Hf or "hno.sub.3" or "h.sub.2o.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:23
S7	14	ultrasonic$7 near16 (silicon near2 carbide or sic) same (Hf or "hno.sub. 3" or "h.sub.2o.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:23
S8	15	ultrasonic$6 near15 (silicon near2 carbide or sic) near10 bath	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:34
S9	13	ultrasonic$6 near15 (HF or hydrogen near2 fluoride) near10 (nitric or "hno. sub.3") and (silicon near2 carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:38
S10	1119	ultrasonic$6 near15 (di or deionized or water) and (silicon near2 carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:39
S11	104	ultrasonic$6 near15 (di or deionized or water) same (silicon near2 carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:41

S12	96	uae	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:42
S13	0	uae near10 hf	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:42
S14	6	uae and ultrasonic$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 15:57
S15	2	"6375752".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 16:15
S16	70	ultrasonic$6 near10 clean$6 near10 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 16:16
S17	1	("5589116").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/22 16:22
S18	14	masashi near2 otsuki.in. and (sic or silicon near2 carbide)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/22 16:25
S19	6	masashi near2 otsuki.in. and (sic or silicon near2 carbide) and ultrasonic$7	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/22 16:25
S20	1	("6419757").URPN.	USPAT	OR	ON	2005/12/22 18:12
S21	0	cvd near10 (sic or silicon near2 carbide) near10 clean$5 near15 ultrasonic$7	USPAT	OR	ON	2005/12/22 18:13
S22	17	cvd near10 (sic or silicon near2 carbide) near10 clean$5	USPAT	OR	ON	2005/12/22 18:13
S23	40	cvd near10 (sic or silicon near2 carbide) near10 clean$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:14

S24	1	cvd near10 (sic or silicon near2 carbide) near10 clean$5 near10 (hf or "hno.sub.3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:25
S25	2	"55158622"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:26
S26	21	"181841"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:26
S27	27	"0181841"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:29
S28	30873	ultrasonic near5 frequency	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:29
S29	777	ultrasonic near5 frequency near10 solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:30
S30	4	ultrasonic near5 frequency near10 solution same (sic or silicon near2 carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:30
S31	130	ning near2 chen.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:31

S32	3	ning near2 chen.in. and (sic or silicon near2 carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:35
S33	4	("6368410" "4957583").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:41
S34	7	(sic or silicon near2 carbide) near10 wafer near10 lift near2 pin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 18:41
S35	8	samantha near2 tan.in. and ultrasonic$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:26
S36	7	samantha near2 tan.in. and multipl$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:27
S37	2	"20030000458".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:29
S38	53	US-3775202-$.DID. OR US-3969195-$. DID. OR US-3986653-$.DID. OR US-3992454-$.DID. OR US-4023936-$. DID. OR US-4078963-$.DID. OR US-4101386-$.DID. OR US-4139348-$. DID. OR US-4197631-$.DID. OR US-4214952-$.DID. OR US-4232060-$. DID. OR US-4272612-$.DID. OR US-4327134-$.DID. OR US-4447824-$. DID. OR US-4448800-$.DID. OR US-4459155-$.DID. OR US-4519914-$. DID. OR US-4530120-$.DID. OR US-4579569-$.DID. OR US-4638553-$. DID. OR US-4699082-$.DID. OR US-4863561-$.DID. OR US-4957583-$. DID. OR US-4971590-$.DID. OR US-4980017-$.DID. OR US-5104501-$. DID. OR US-5152878-$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:31

S39	40	US-5221421-$.DID. OR US-5516399-$.DID. OR US-5593339-$.DID. OR US-5614027-$.DID. OR US-5665473-$.DID. OR US-5712198-$.DID. OR US-5744214-$.DID. OR US-5766979-$.DID. OR US-5840402-$.DID. OR US-5888308-$.DID. OR US-5908819-$.DID. OR US-5929521-$.DID. OR US-5966593-$.DID. OR US-6012966-$.DID. OR US-6187216-$.DID. OR US-6368410-$.DID. OR US-6506254-$.DID. OR US-6569252-$.DID. OR US-6579153-$.DID. OR US-6767840-$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:40
S40	0	clean$6 near10 (sic or silicon near2 carbide) near16 acid$5 near16 (multipl$6 or plural$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:40
S41	322	clean$6 near16 acid$5 near16 (multipl$6 or plural$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:41
S42	25	clean$6 near16 acid$5 near16 (multipl$6 or plural$6) same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:41
S43	2278	(sic or silicon near2 carbide) near10 (roof or dome or ring or collar)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:42
S44	15	(sic or silicon near2 carbide) near10 (roof or dome or ring or collar) near15 clean$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:44
S45	75	(sic or silicon near2 carbide) near10 (roof or dome or ring or collar) near15 (cvd or chemical near2 vapor near2 deposit$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:45
S46	2	"5904778".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:46

S47	45	clean$5 near10 chamber near2 roof	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:47
S48	30	clean$5 near10 apparatus near10 (silicon near2 carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:48
S49	1	clean$5 near10 apparatus near10 (silicon near2 carbide or sic) same solution	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:48
S51	145	clean$5 near10 apparatus near15 ultrasonic$6 same (multipl$5 or plural$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:51
S52	1	clean$5 near10 apparatus near15 ultrasonic$6 near15 boat$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:51
S53	180	clean$5 near10 apparatus near15 boat$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:51
S54	4	clean$5 near10 apparatus near15 boat$6 near15 acid$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:52
S55	24	clean$5 near10 wafer near15 boat$6 near15 acid$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:52
S56	2440	ultrasonic$6 near10 rins$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 16:35
S57	1325	ultrasonic$6 near10 rins$6 near10 (DI or water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 16:35

S58	1104	ultrasonic$6 near10 rins$6 near2 (DI or water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 16:35
S59	214	ultrasonic$6 near2 rins$6 near2 (DI or water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 16:35
S60	131	ultrasonic$6 near2 rins$6 near2 (DI or water) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 16:36
S61	1	ultrasonic$6 near2 rins$6 near2 (DI or water) near15 (advantag$6 or improv$5) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 16:36
S62	1	ultrasonic$6 near2 rins$6 near2 (DI or water) near15 (advantag$6 or improv$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 16:36
S63	9	ultrasonic$6 near2 rins$6 near15 (advantag$6 or improv$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 16:36
S64	3	bak$3 near10 nitrogen near2 purge near5 oven	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 10:50
S65	162	bak$3 near10 nitrogen near5 oven	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 10:50
S66	27	bak$3 near10 nitrogen near5 oven same rins$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 10:53
S67	38	bak$3 near10 convection near5 oven same rins$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 10:55

S68	78	bak$3 near10 vacuum near5 oven same rins$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 10:57
S69	8	bak$3 near10 vacuum near5 oven same rins$5 near15 ultrasonic$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 10:58
S70	3	bak$3 near10 vacuum near5 oven same clean$5 and silicon near2 carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:00
S71	34	clean$5 near15 lift near2 pin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:00
S72	1273	convection near5 oven near16 dry$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:11
S73	0	convection near5 oven near16 dry$6 and clean$5 near15 ceraminc	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:11
S74	5	convection near5 oven near16 dry$6 and clean$5 near15 ceramic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:24
S75	5237	pin near4 rack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:24
S76	8	pin near4 rack and silicon near2 carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:24
S77	56	pin near4 rack same clean$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:25

S78	3	pin near4 rack same etch$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:30
S79	22	oxidiz$5 near15 (sic or silicon near2 carbide) near20 clean$56	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:30
S80	21	oxidiz$5 near15 (sic or silicon near2 carbide) near20 clean$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:32
S81	65	scrub$6 near15 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:46
S82	9	scrub$6 near15 (sic or silicon near2 carbide) near15 clean$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:46
S83	122	(cmp or polish$6) near15 (sic or silicon near2 carbide) near15 clean$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:51
S84	21	wafer near10 cassette same polyethylene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:53
S85	56	wafer same polyethylene near5 high near2 density	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 11:53
S86	2	wafer and cassette same polyethylene near5 high near2 density	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 12:11
S87	273	clean$5 near10 showerhead	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 12:11

S88	178	clean$5 near10 showerhead and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 12:11
S89	62	clean$5 near10 showerhead same etch$5 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 12:12
S90	0	clean$5 near10 showerhead near15 etch$5 near5 (wet or bath)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 12:12
S91	0	clean$5 near10 showerhead same etch$5 near5 (wet or bath)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 12:12
S92	0	showerhead near15 etch$5 near5 (wet or bath)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/19 12:12
S93	2	showerhead near16 dip$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 17:37